

Characterization of grain boundaries in silicon

National Aeronautics and Space Administration, Jet Propulsion Laboratory, California
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Description: -

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Steel

Naval Submarine Base Bangor (Wash.) -- Environmental aspects

United States -- Claims

Bills, Private -- United States

United States. -- Congress -- Private bills

Spectroscopic analysis.

Silicon.

Polycrystals.

Photoconductivity.

Grain boundaries.

Electrical properties.

Grain boundaries.

Silicon.

Flat-plate Solar Array Project.Characterization of grain boundaries in silicon

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NASA contractor report -- NASA CR-173459.

NASA-CR -- 173459.

JPL publication -- 83-87.Characterization of grain boundaries in silicon

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Tags: #Characterization #of
#polycrystalline #silicon #grain #boundary
#structures #by #optical #second
#harmonic #generation

Grain Boundary Data Archive: Silicon

Ausgangspunkt für die Bestimmung der Zustandsdichte und der Energieverteilung von Korngrenzen-Zuständen sind die Ergebnisse für die Höhe der Potentialbarriere an den Korngrenzen von Solarzellenmaterial. This surface was suitable for electron backscatter diffraction EBSD analysis without further treatment.

Characterization of grain boundaries in silicon solar cells

For incoherent $\hat{\text{E}}3$ GBs, a strong pan-CL and EBIC contrast was observed in the entire temperature range. Conductive AFM measurements are furthermore compared to data obtained by electron beam induced current EBIC, indicating that cAFM provides complimentary information. The light-beam-induced current can be calibrated to give the spatially resolved quantum yield.

Characterization of grain boundaries in silicon solar cells

The axis angle distribution, at the specified misorientation angles.

Characterization of grain boundaries in multicrystalline silicon with high lateral resolution using conductive atomic force microscopy

The technique we developed uses a short-arc xenon lamp source with line spectra. From this numerical simulation the influence of the various parameters on the signal properties is deduced.

Characterization of grain boundaries in silicon solar cells

Eine Bikristall-Teststruktur, die aus SILSO-Solarzellenmaterial herauspräpariert worden ist, wurde unter elektrischer Anregung untersucht. Part 2:

Evaluation of the density of grain boundary states. You have requested a machine translation of selected content from our databases.

Characterization of polycrystalline silicon grain boundary structures by optical second harmonic generation

Translations are not retained in our system. The compressed folder is 236 MB and contains 29 fields of view. Bei dieser Bestimmung der Energieverteilung der Zustandsdichte von Korngrenzen-Zuständen handelt es sich um eine spektroskopische Methode, die den Gesamtverlauf in diskontinuierlichen Stufen beschreibt.

Characterization of grain boundaries in silicon solar cells

Signals and deduced characteristic values, i.

Characterization of grain boundaries in multicrystalline silicon with high lateral resolution using conductive atomic force microscopy

The method is a spectroscopic one and yields a steplike energy distribution. Proceeding from the results for the barrier height of a grain boundary in solar cell material evaluated from the measurement of the zero bias conductance at a bicrystal test structure the density of grain boundary states and their distribution in energy have been determined.

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